

CSD18504Q5A 40V N-Channel NexFET™ Power MOSFET

1 Features

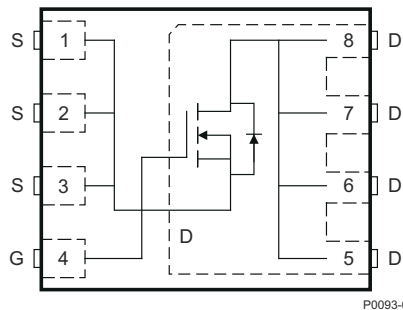
- Ultra-low Q_g and Q_{gd}
- Low thermal resistance
- Avalanche rated
- Logic level
- Pb free terminal plating
- RoHS compliant
- Halogen free
- SON 5mm × 6mm plastic package

2 Applications

- DC-DC conversion
- Secondary side synchronous rectifier
- Battery motor control

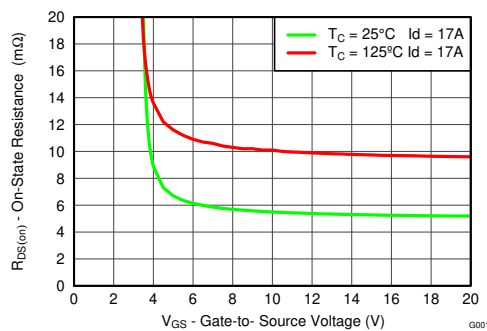
3 Description

This 5.3m Ω , SON 5mm × 6mm, 40V NexFET™ power MOSFET is designed to minimize losses in power conversion applications.

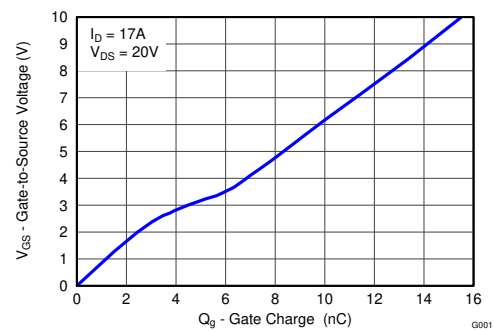


P0093-01

Top View



$R_{DS(on)}$ vs V_{GS}



Gate Charge

Product Summary

$T_A = 25^\circ\text{C}$		TYPICAL VALUE		UNIT
V_{DS}	Drain-to-Source Voltage	40		V
Q_g	Gate Charge Total (4.5V)	7.7		nC
Q_{gd}	Gate Charge Gate-to-Drain	2.4		nC
$R_{DS(on)}$	Drain-to-Source On-Resistance	$V_{GS} = 4.5\text{V}$	7.5	m Ω
		$V_{GS} = 10\text{V}$	5.3	m Ω
$V_{GS(th)}$	Threshold Voltage	1.9		V

Ordering Information (1)

Device	Qty	Media	Package	Ship
CSD18504Q5A	2500	13-Inch Reel	SON 5mm × 6mm Plastic Package	Tape and Reel
CSD18504Q5AT	250	7-Inch Reel		

- (1) For all available packages, see the orderable addendum at the end of the data sheet.

Absolute Maximum Ratings

$T_A = 25^\circ\text{C}$		VALUE	UNIT
V_{DS}	Drain-to-Source Voltage	40	V
V_{GS}	Gate-to-Source Voltage	±20	V
I_D	Continuous Drain Current (Package limited)	50	A
	Continuous Drain Current (Silicon limited), $T_C = 25^\circ\text{C}$	75	
	Continuous Drain Current ⁽¹⁾	15	
I_{DM}	Pulsed Drain Current ⁽²⁾	275	A
P_D	Power Dissipation ⁽¹⁾	3.1	W
	Power Dissipation, $T_C = 25^\circ\text{C}$	77	
T_J , T_{stg}	Operating Junction and Storage Temperature Range	–55 to 150	°C
E_{AS}	Avalanche Energy, single pulse $I_D = 43\text{A}$, $L = 0.1\text{mH}$, $R_G = 25\Omega$	92	mJ

- (1) Typical $R_{\theta JA} = 40^\circ\text{C/W}$ on a 1-inch², 2oz. Cu pad on a 0.06-inch thick FR4 PCB.
(2) Max $R_{\theta JC} = 2.0^\circ\text{C/W}$, pulse duration $\leq 100\mu\text{s}$, duty cycle $\leq 1\%$



Table of Contents

1 Features	1	5.2 Documentation Support.....	7
2 Applications	1	5.3 Receiving Notification of Documentation Updates.....	7
3 Description	1	5.4 Support Resources.....	7
4 Specifications	3	5.5 Trademarks.....	7
4.1 Electrical Characteristics.....	3	5.6 Electrostatic Discharge Caution.....	7
4.2 Thermal Information.....	3	5.7 Glossary.....	7
4.3 Typical MOSFET Characteristics.....	4	6 Revision History	8
5 Device and Documentation Support	7	7 Mechanical, Packaging, and Orderable Information	9
5.1 Third-Party Products Disclaimer.....	7		

4 Specifications

4.1 Electrical Characteristics

(T_A = 25°C unless otherwise stated)

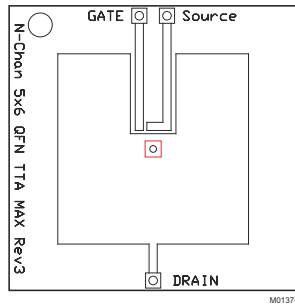
PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
STATIC CHARACTERISTICS						
BV _{DSS}	Drain-to-Source Voltage	V _{GS} = 0V, I _D = 250μA	40			V
I _{DSS}	Drain-to-Source Leakage Current	V _{GS} = 0V, V _{DS} = 32V			1	μA
I _{GSS}	Gate-to-Source Leakage Current	V _{DS} = 0V, V _{GS} = 20V			100	nA
V _{GS(th)}	Gate-to-Source Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	1.5	1.9	2.4	V
R _{DS(on)}	Drain-to-Source On-Resistance	V _{GS} = 4.5V, I _D = 17A		7.5	9.8	mΩ
		V _{GS} = 10V, I _D = 17A		5.3	6.6	mΩ
g _{fs}	Transconductance	V _{DS} = 20V, I _D = 17A		71		S
DYNAMIC CHARACTERISTICS						
C _{iss}	Input Capacitance	V _{GS} = 0V, V _{DS} = 20V, f = 1MHz		1380	1656	pF
C _{oss}	Output Capacitance			310	372	pF
C _{rss}	Reverse Transfer Capacitance			8	9.6	pF
R _G	Series Gate Resistance			1.4	2.8	Ω
Q _g	Gate Charge Total (4.5V)	V _{DS} = 20V, I _D = 17A		7.7	9.2	nC
Q _g	Gate Charge Total (10V)			16	19	
Q _{gd}	Gate Charge Gate-to-Drain			2.4		nC
Q _{gs}	Gate Charge Gate-to-Source			3.2		nC
Q _{g(th)}	Gate Charge at V _{th}			2.2		nC
Q _{oss}	Output Charge		V _{DS} = 20V, V _{GS} = 0V		21	
t _{d(on)}	Turn On Delay Time	V _{DS} = 20V, V _{GS} = 10V, I _{DS} = 17A, R _G = 0Ω		3.2		ns
t _r	Rise Time			6.8		ns
t _{d(off)}	Turn Off Delay Time			12		ns
t _f	Fall Time			2		ns
DIODE CHARACTERISTICS						
V _{SD}	Diode Forward Voltage	I _{SD} = 17A, V _{GS} = 0V		0.8	1	V
Q _{rr}	Reverse Recovery Charge	V _{DS} = 20V, I _F = 17A, di/dt = 300A/μs		39		nC
t _{rr}	Reverse Recovery Time			28		ns

4.2 Thermal Information

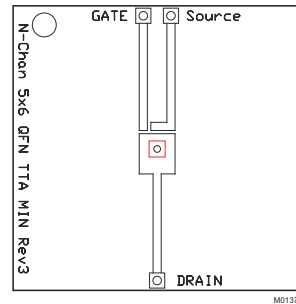
(T_A = 25°C unless otherwise stated)

THERMAL METRIC		MIN	TYP	MAX	UNIT
R _{θJC}	Junction-to-Case Thermal Resistance ⁽¹⁾			2.0	°C/W
R _{θJA}	Junction-to-Ambient Thermal Resistance ^{(1) (2)}			50	

- (1) R_{θJC} is determined with the device mounted on a 1-inch² (6.45cm²), 2oz. (0.071mm thick) Cu pad on a 1.5-inches × 1.5-inches (3.81cm × 3.81cm), 0.06-inch (1.52mm) thick FR4 PCB. R_{θJC} is specified by design, whereas R_{θJA} is determined by the user's board design.
- (2) Device mounted on FR4 material with 1-inch² (6.45cm²), 2oz. (0.071mm thick) Cu.



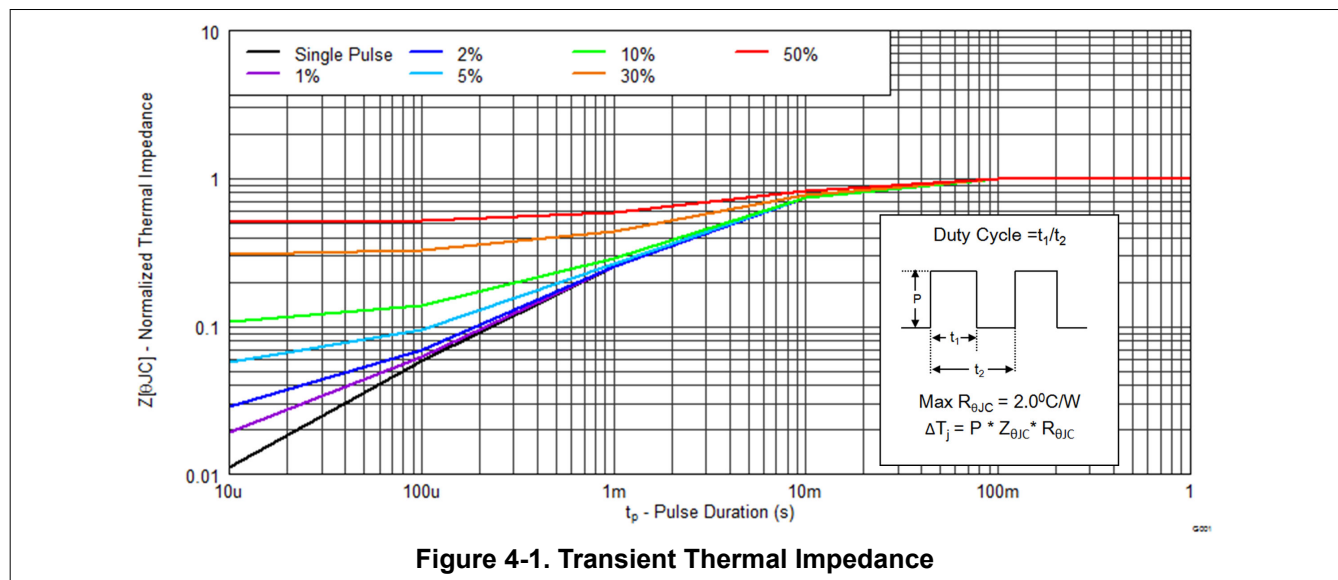
Max $R_{\theta JA} = 50^{\circ}\text{C/W}$
when mounted on 1 inch²
(6.45cm²) of
2oz. (0.071mm thick) Cu.



Max $R_{\theta JA} = 125^{\circ}\text{C/W}$ when
mounted on a minimum pad
area of
2oz. (0.071mm thick) Cu.

4.3 Typical MOSFET Characteristics

($T_A = 25^{\circ}\text{C}$ unless otherwise stated)



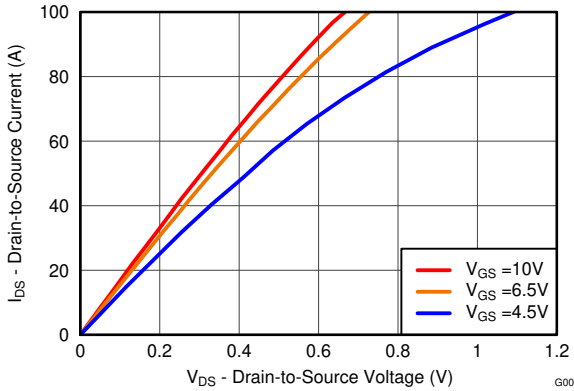


Figure 4-2. Saturation Characteristics

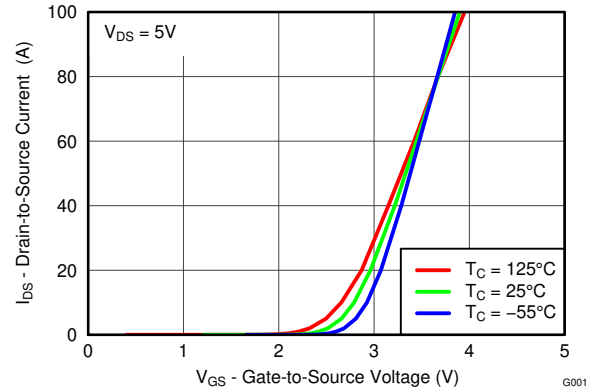


Figure 4-3. Transfer Characteristics

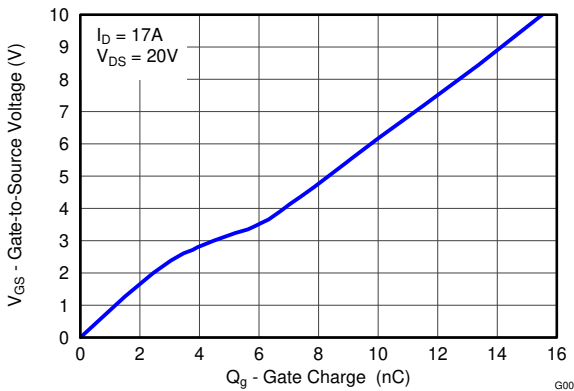


Figure 4-4. Gate Charge

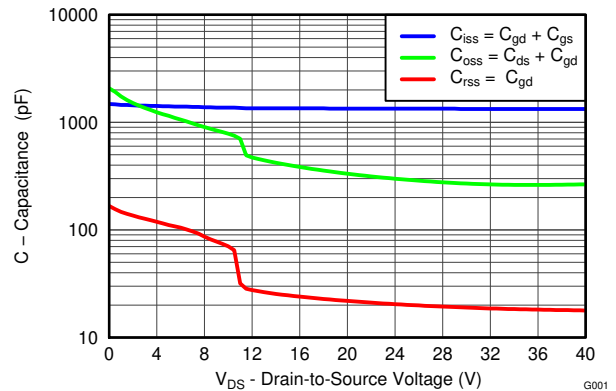


Figure 4-5. Capacitance

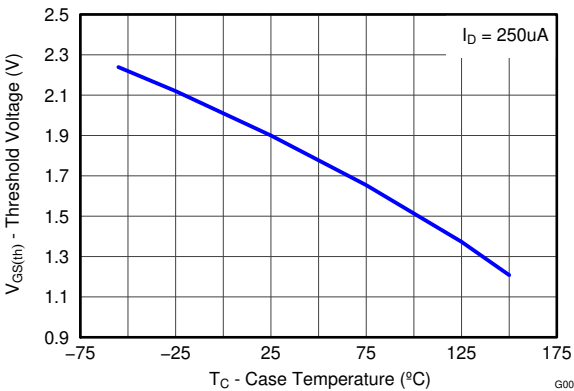


Figure 4-6. Threshold Voltage vs Temperature

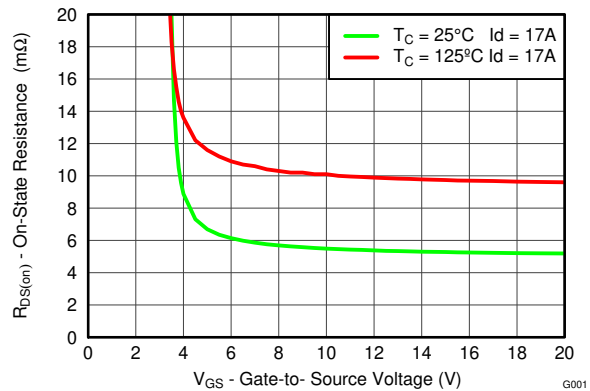


Figure 4-7. On-State Resistance vs Gate-to-Source Voltage

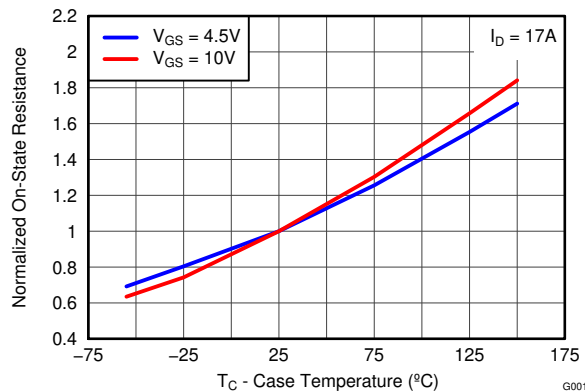


Figure 4-8. Normalized On-State Resistance vs Temperature

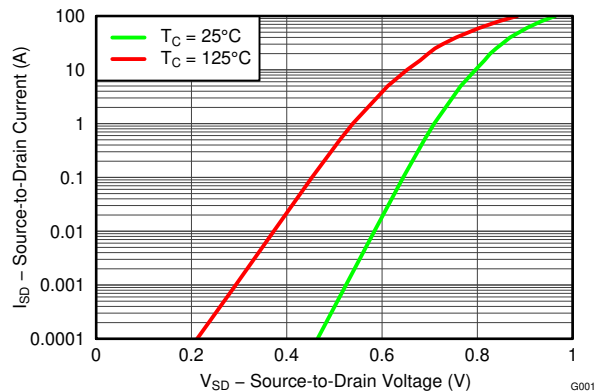


Figure 4-9. Typical Diode Forward Voltage

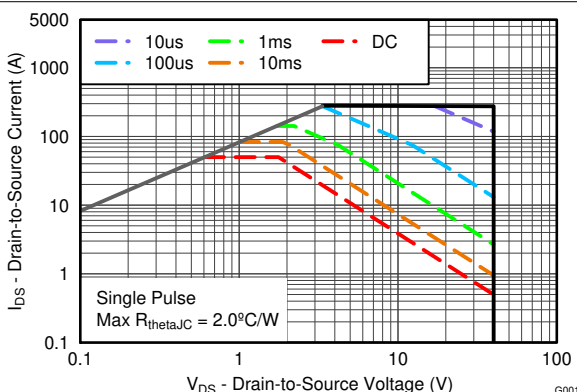


Figure 4-10. Maximum Safe Operating Area

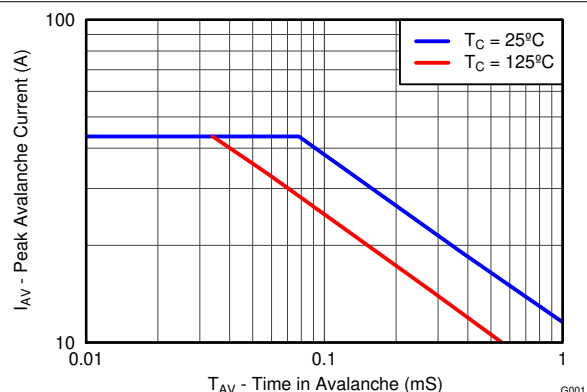


Figure 4-11. Single Pulse Unclamped Inductive Switching

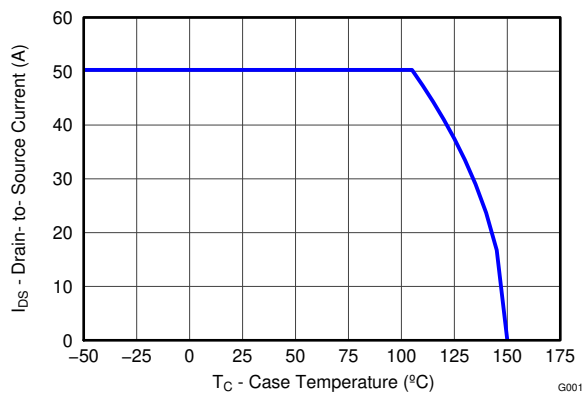


Figure 4-12. Maximum Drain Current vs Temperature

5 Device and Documentation Support

5.1 Third-Party Products Disclaimer

TI'S PUBLICATION OF INFORMATION REGARDING THIRD-PARTY PRODUCTS OR SERVICES DOES NOT CONSTITUTE AN ENDORSEMENT REGARDING THE SUITABILITY OF SUCH PRODUCTS OR SERVICES OR A WARRANTY, REPRESENTATION OR ENDORSEMENT OF SUCH PRODUCTS OR SERVICES, EITHER ALONE OR IN COMBINATION WITH ANY TI PRODUCT OR SERVICE.

5.2 Documentation Support

5.2.1 Related Documentation

5.3 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

5.4 Support Resources

[TI E2E™ support forums](#) are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

5.5 Trademarks

NexFET™ is a trademark of Texas Instruments.

TI E2E™ is a trademark of Texas Instruments.

All trademarks are the property of their respective owners.

5.6 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

5.7 Glossary

[TI Glossary](#) This glossary lists and explains terms, acronyms, and definitions.

6 Revision History

Changes from Revision E (August 2014) to Revision F (January 2025) Page

- Updated the numbering format for tables, figures, and cross-references throughout the document..... 1

Changes from Revision D (August 2014) to Revision E (August 2014) Page

- Increased pulsed current to 275A 1
- Updated the SOA in [Figure 4-10](#) 4

Changes from Revision C (May 2013) to Revision D (August 2014) Page

- Added 7-inch reel to Ordering Information table 1
- Added parameter for power dissipation with case temperature held to 25°C 1
- Updated pulsed current conditions 1
- Updated [Figure 4-1](#) to a normalized $R_{\theta JC}$ curve..... 4

Changes from Revision B (November 2012) to Revision C (May 2013) Page

- Updated Mechanical stencil..... 9

Changes from Revision A (October 2012) to Revision B (November 2012) Page

- Changed the $R_{DS(on)}$ vs V_{GS} and Gate Charge graphs..... 1
- Changed $R_{\theta JA}$ Max value From: 51 To: 50°C/W..... 3
- Changed the Typical MOSFET Characteristics section..... 4

Changes from Revision * (June 2012) to Revision A (October 2012) Page

- Changed the Transconductance TYP value From: 63S To: 71S..... 3
- Changed the Turn On and Turn Off Delay Time, Rise and Fall Time Test Conditions From: $I_{DS} = 17A$, $R_G = 2\Omega$ To: $I_{DS} = 17A$, $R_G = 0\Omega$ 3
- Changed the Q_{rr} Reverse Recovery Charge TYP value From: 18nC To: 39nC..... 3

7 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
CSD18504Q5A	Active	Production	VSONP (DQJ) 8	2500 LARGE T&R	ROHS Exempt	SN	Level-1-260C-UNLIM	-55 to 150	CSD18504
CSD18504Q5A.B	Active	Production	VSONP (DQJ) 8	2500 LARGE T&R	ROHS Exempt	SN	Level-1-260C-UNLIM	-55 to 150	CSD18504
CSD18504Q5AT	Active	Production	VSONP (DQJ) 8	250 SMALL T&R	ROHS Exempt	SN	Level-1-260C-UNLIM	-55 to 150	CSD18504
CSD18504Q5AT.B	Active	Production	VSONP (DQJ) 8	250 SMALL T&R	ROHS Exempt	SN	Level-1-260C-UNLIM	-55 to 150	CSD18504

⁽¹⁾ **Status:** For more details on status, see our [product life cycle](#).

⁽²⁾ **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

⁽⁴⁾ **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "-" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL INFORMATION



*All dimensions are nominal

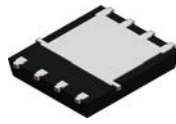
Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD18504Q5A	VSONP	DQJ	8	2500	330.0	12.4	6.3	5.3	1.2	8.0	12.0	Q1
CSD18504Q5AT	VSONP	DQJ	8	250	180.0	12.4	6.3	5.3	1.2	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS

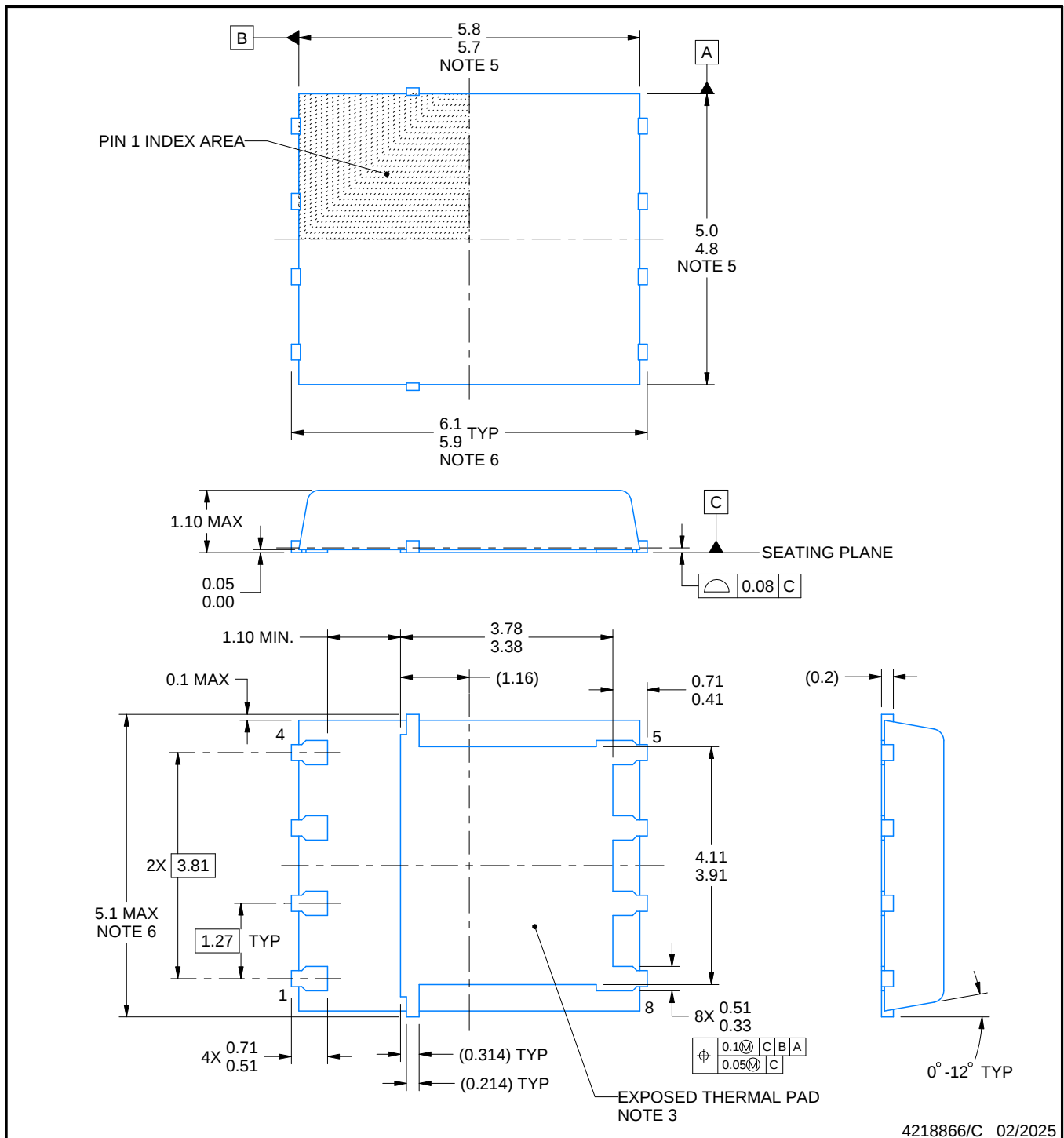


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CSD18504Q5A	VSONP	DQJ	8	2500	340.0	340.0	38.0
CSD18504Q5AT	VSONP	DQJ	8	250	190.0	190.0	30.0

DQJ0008A**PACKAGE OUTLINE****VSONP - 1.1 mm max height**

PLASTIC SMALL OUTLINE - NO LEAD



4218866/C 02/2025

NOTES:

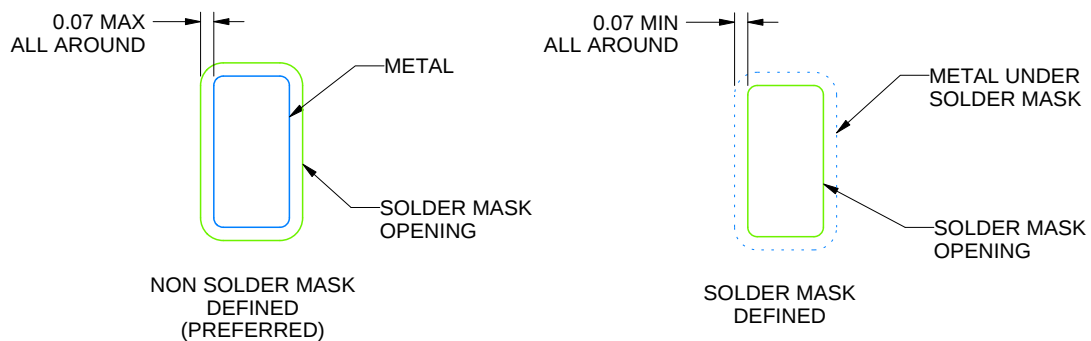
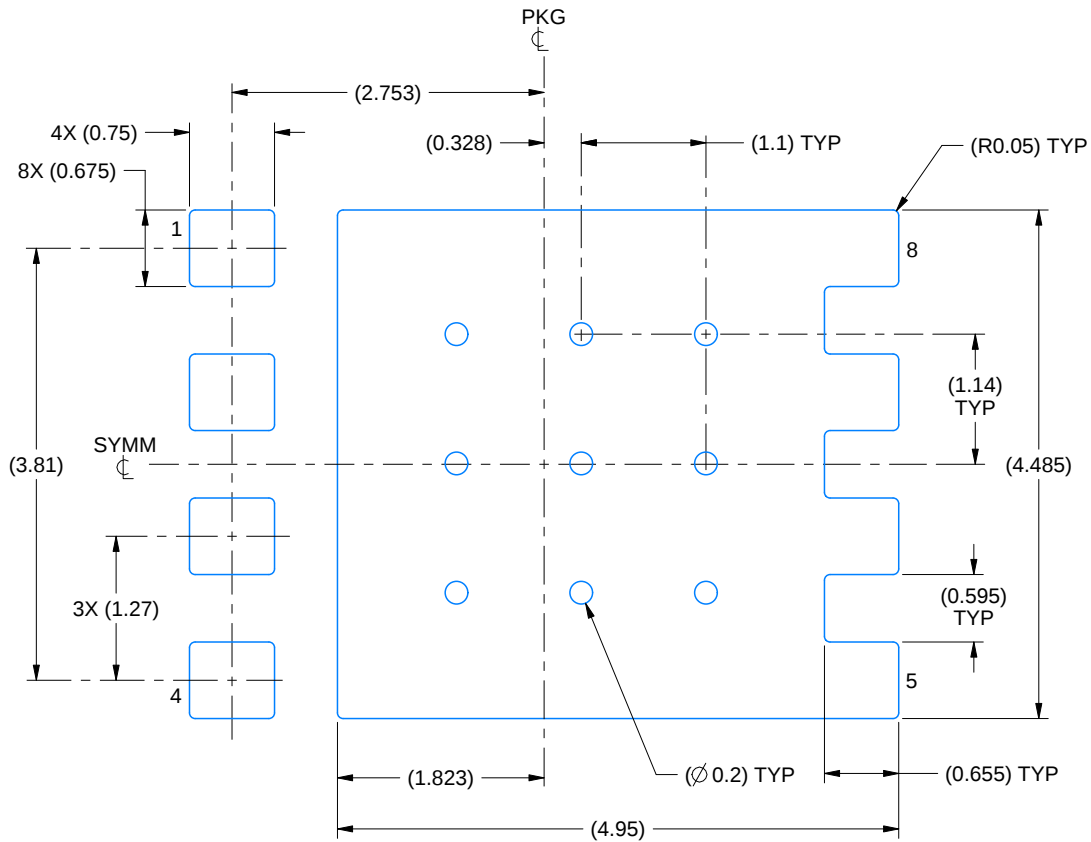
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.
4. Metalized features are supplier options and may not be on the package.
5. These dimensions do not include mold flash protrusions or gate burrs.
6. These dimensions include interterminal flash or protrusion. Interterminal flash or protrusion shall not exceed 0.25 mm per side.

EXAMPLE BOARD LAYOUT

DQJ0008A

VSONP - 1.1 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



SOLDER MASK DETAILS

4218866/C 02/2025

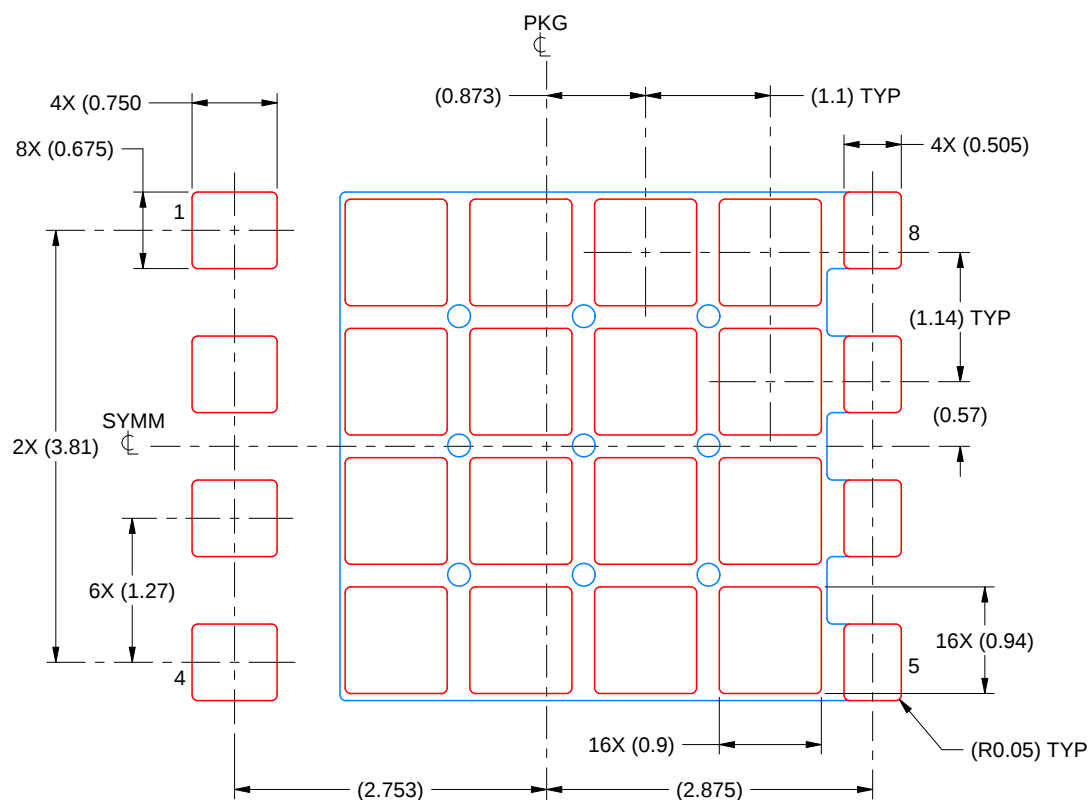
NOTES: (continued)

7. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/sluea271).
8. Vias are optional depending on application, refer to device data sheet. If some or all are implemented, recommended via locations are shown.

DQJ0008A

VSONP - 1.1 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD:
70% PRINTED SOLDER COVERAGE BY AREA UNDER PACKAGE
SCALE: 15X

4218866/C 02/2025

NOTES: (continued)

9. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATA SHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, regulatory or other requirements.

These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you will fully indemnify TI and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to [TI's Terms of Sale](#) or other applicable terms available either on [ti.com](https://www.ti.com) or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products.

TI objects to and rejects any additional or different terms you may have proposed.

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265
Copyright © 2025, Texas Instruments Incorporated